

# Giovanni Ghione

## List of Publications by Year in descending order

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256  
papers

4,308  
citations

147566

31  
h-index

155451

55  
g-index

263  
all docs

263  
docs citations

263  
times ranked

2588  
citing authors

#	ARTICLE	IF	CITATIONS
1	Monte Carlo simulation of electron transport in the III-nitride wurtzite phase materials system: binaries and ternaries. IEEE Transactions on Electron Devices, 2001, 48, 535-542.	1.6	376
2	Coplanar Waveguides for MMIC Applications: Effect of Upper Shielding, Conductor Backing, Finite-Extent Ground Planes, and Line-to-Line Coupling. IEEE Transactions on Microwave Theory and Techniques, 1987, 35, 260-267.	2.9	305
3	Analytical formulas for coplanar lines in hybrid and monolithic MICs. Electronics Letters, 1984, 20, 179.	0.5	178
4	3.6-GHz Wideband GaN Doherty Power Amplifier Exploiting Output Compensation Stages. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 2543-2548.	2.9	131
5	An efficient approach to noise analysis through multidimensional physics-based models. IEEE Transactions on Electron Devices, 1998, 45, 261-269.	1.6	121
6	Band structure nonlocal pseudopotential calculation of the III-nitride wurtzite phase materials system. Part I. Binary compounds GaN, AlN, and InN. Journal of Applied Physics, 2000, 88, 6467-6475.	1.1	113
7	A CAD-oriented analytical model for the losses of general asymmetric coplanar lines in hybrid and monolithic MICs. IEEE Transactions on Microwave Theory and Techniques, 1993, 41, 1499-1510.	2.9	110
8	Parameters of coplanar waveguides with lower ground plane. Electronics Letters, 1983, 19, 734.	0.5	107
9	Noise in Semiconductor Devices. Springer Series in Advanced Microelectronics, 2001, , .	0.3	92
10	Band structure nonlocal pseudopotential calculation of the III-nitride wurtzite phase materials system. Part II. Ternary alloys $\text{Al}_x\text{Ga}_{1-x}\text{N}$ , $\text{In}_x\text{Ga}_{1-x}\text{N}$ , and $\text{In}_x\text{Al}_{1-x}\text{N}$ . Journal of Applied Physics, 2000, 88, 6476-6482.	1.1	86
11	Physics-based modeling and experimental implications of trap-assisted tunneling in InGaN/GaN light-emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 947-953.	0.8	77
12	On the application of the Kirchhoff transformation to the steady-state thermal analysis of semiconductor devices with temperature-dependent and piecewise inhomogeneous thermal conductivity. Solid-State Electronics, 1995, 38, 1409-1412.	0.8	76
13	A TCAD approach to the physics-based modeling of frequency conversion and noise in semiconductor devices under large-signal forced operation. IEEE Transactions on Electron Devices, 2001, 48, 966-977.	1.6	64
14	Generation-recombination noise modelling in semiconductor devices through population or approximate equivalent current density fluctuations. Solid-State Electronics, 1999, 43, 285-295.	0.8	52
15	Ag nanoparticle-based inkjet printed planar transmission lines for RF and microwave applications: Considerations on ink composition, nanoparticle size distribution and sintering time. Microelectronic Engineering, 2012, 97, 8-15.	1.1	51
16	Auger recombination in InGaN/GaN quantum wells: A full-Brillouin-zone study. Applied Physics Letters, 2013, 103, 081106.	1.5	51
17	Self-Consistent Electrothermal Modeling of Class A, AB, and B Power GaN HEMTs Under Modulated RF Excitation. IEEE Transactions on Microwave Theory and Techniques, 2007, 55, 1824-1831.	2.9	47
18	Microwave modeling and characterization of thick coplanar waveguides on oxide-coated lithium niobate substrates for electrooptical applications. IEEE Transactions on Microwave Theory and Techniques, 1999, 47, 2287-2293.	2.9	45

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19	Effect of Load Modulation on Phase Distortion in Doherty Power Amplifiers. IEEE Microwave and Wireless Components Letters, 2014, 24, 505-507.	2.0	43
20	Modeling of multiconductor buses and analysis of crosstalk, propagation delay and pulse distortion in high speed GaAs logic circuits. IEEE Transactions on Microwave Theory and Techniques, 1989, 37, 445-456.	2.9	42
21	A computationally efficient unified approach to the numerical analysis of the sensitivity and noise of semiconductor devices. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 1993, 12, 425-438.	1.9	42
22	Physical modeling of GaAs MESFETs in an integrated CAD environment: from device technology to microwave circuit performance. IEEE Transactions on Microwave Theory and Techniques, 1989, 37, 457-468.	2.9	41
23	Physics-based electron device modelling and computer-aided MMIC design. IEEE Transactions on Microwave Theory and Techniques, 1992, 40, 1333-1352.	2.9	39
24	A fast reduced-order model for the full-wave FEM analysis of lossy inhomogeneous anisotropic waveguides. IEEE Transactions on Microwave Theory and Techniques, 2002, 50, 2108-2114.	2.9	39
25	Hydrodynamic transport parameters of wurtzite ZnO from analytic- and full-band Monte Carlo simulation. Solid-State Electronics, 2008, 52, 1796-1801.	0.8	39
26	Physics-based simulation techniques for small- and large-signal device noise analysis in RF applications. IEEE Transactions on Electron Devices, 2003, 50, 633-644.	1.6	37
27	Experimental validation of GaN HEMTs thermal management by using photocurrent measurements. IEEE Transactions on Electron Devices, 2006, 53, 182-188.	1.6	35
28	Physics-Based PiN Diode SPICE Model for Power-Circuit Simulation. IEEE Transactions on Industry Applications, 2007, 43, 911-919.	3.3	35
29	Numerical Modeling of SRH and Tunneling Mechanisms in High-Operating-Temperature MWIR HgCdTe Photodetectors. Journal of Electronic Materials, 2015, 44, 3056-3063.	1.0	35
30	Semiclassical simulation of trap-assisted tunneling in GaN-based light-emitting diodes. Journal of Computational Electronics, 2015, 14, 444-455.	1.3	34
31	Noise source modeling for cyclostationary noise analysis in large-signal device operation. IEEE Transactions on Electron Devices, 2002, 49, 1640-1647.	1.6	33
32	Revisiting the partial-capacitance approach to the analysis of coplanar transmission lines on multilayered substrates. IEEE Transactions on Microwave Theory and Techniques, 2003, 51, 2007-2014.	2.9	33
33	A Unified Approach to the Sensitivity and Variability Physics-Based Modeling of Semiconductor Devices Operated in Dynamic Conditionsâ€”Part I: Large-Signal Sensitivity. IEEE Transactions on Electron Devices, 2016, 63, 1195-1201.	1.6	31
34	A novel smart caliper foam pig for low-cost pipeline inspectionâ€”Part A: Design and laboratory characterization. Journal of Petroleum Science and Engineering, 2015, 127, 311-317.	2.1	30
35	Looking for Auger signatures in III-nitride light emitters: A full-band Monte Carlo perspective. Applied Physics Letters, 2015, 106, .	1.5	30
36	A general conformal-mapping approach to the optimum electrode design of coplanar waveguides with arbitrary cross section. IEEE Transactions on Microwave Theory and Techniques, 2001, 49, 1573-1580.	2.9	29

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37	Correlating electroluminescence characterization and physics-based models of InGaN/GaN LEDs: Pitfalls and open issues. AIP Advances, 2014, 4, .	0.6	29
38	RF power performance evaluation of surface channel diamond MESFETs. Solid-State Electronics, 2011, 55, 19-24.	0.8	28
39	Linear GaN MMIC Combined Power Amplifiers for 7-GHz Microwave Backhaul. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 2700-2710.	2.9	28
40	Transfer matrix method modelling of inhomogeneous Schottky barrier diodes on silicon carbide. Solid-State Electronics, 2007, 51, 466-474.	0.8	27
41	A 4-W Doherty Power Amplifier in GaN MMIC Technology for 15-GHz Applications. IEEE Microwave and Wireless Components Letters, 2017, 27, 365-367.	2.0	27
42	Analytic determination of the capacitance matrix of planar or cylindrical multiconductor lines on multilayered substrates. IEEE Transactions on Microwave Theory and Techniques, 1995, 43, 363-373.	2.9	26
43	Experimental demonstration of a balanced electroabsorption modulated microwave photonic link. IEEE Transactions on Microwave Theory and Techniques, 2001, 49, 1956-1961.	2.9	26
44	GaN transistor characterization and modeling activities performed within the frame of the KorriGaN project. International Journal of Microwave and Wireless Technologies, 2010, 2, 51-61.	1.5	25
45	Two-dimensional finite-boxes analysis of monopolar corona fields including ion diffusion. IEEE Transactions on Magnetics, 1990, 26, 567-570.	1.2	24
46	Microwave modeling and characterization of thick coplanar waveguides on oxide-coated lithium niobate substrates for electro-optical applications. , 0, , .		24
47	A Unified Approach to the Sensitivity and Variability Physics-Based Modeling of Semiconductor Devices Operated in Dynamic Conditions. Part II – Small-Signal and Conversion Matrix Sensitivity. IEEE Transactions on Electron Devices, 2016, 63, 1202-1208.	1.6	24
48	Fabrication and nonlinear characterization of GaN HEMTs on SiC and sapphire for high-power applications. International Journal of RF and Microwave Computer-Aided Engineering, 2006, 16, 70-80.	0.8	23
49	On the Substrate Thermal Optimization in SiC-Based Backside-Mounted High-Power GaN FETs. IEEE Transactions on Electron Devices, 2007, 54, 1744-1752.	1.6	23
50	Discretization schemes for high-frequency semiconductor device models. IEEE Transactions on Antennas and Propagation, 1997, 45, 443-456.	3.1	22
51	Efficient quasi-TEM frequency-dependent analysis of lossy multiconductor lines through a fast reduced-order FEM model. IEEE Transactions on Microwave Theory and Techniques, 2003, 51, 2029-2035.	2.9	22
52	Simulation of Small-Pitch HgCdTe Photodetectors. Journal of Electronic Materials, 2017, 46, 5458-5470.	1.0	22
53	The influence of ground-plane width on the ohmic losses of coplanar waveguides with finite lateral ground planes. IEEE Transactions on Microwave Theory and Techniques, 1997, 45, 1640-1642.	2.9	21
54	Comparing FDTD and Ray-Tracing Models in Numerical Simulation of HgCdTe LWIR Photodetectors. Journal of Electronic Materials, 2016, 45, 4524-4531.	1.0	20

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55	Diffusive-Probabilistic Model for Inter-Pixel Crosstalk in HgCdTe Focal Plane Arrays. IEEE Journal of the Electron Devices Society, 2018, 6, 664-673.	1.2	20
56	Complex ray analysis of radiation from large apertures with tapered illumination. IEEE Transactions on Antennas and Propagation, 1984, 32, 684-693.	0.8	19
57	Physics-based large-signal sensitivity analysis of microwave circuits using technological parametric sensitivity from multidimensional semiconductor device models. IEEE Transactions on Microwave Theory and Techniques, 1997, 45, 846-855.	2.9	19
58	Physics-based mixed-mode reverse recovery modeling and optimization of Si PiN and MPS fast recovery diodes. Microelectronics Journal, 2006, 37, 190-196.	1.1	19
59	Broad-band coaxial directional couplers for high-power applications. IEEE Transactions on Microwave Theory and Techniques, 2003, 51, 994-997.	2.9	18
60	Self-consistent time-domain large-signal model of high-speed traveling-wave electroabsorption modulators. IEEE Transactions on Microwave Theory and Techniques, 2003, 51, 1096-1104.	2.9	18
61	A 20 Watt Micro-strip X-Band AlGaIn/GaN HPA MMIC for Advanced Radar Applications. , 2008, , .		18
62	Carrier capture in InGaIn/GaN quantum wells: Role of electron-electron scattering. Journal of Applied Physics, 2017, 121, 123107.	1.1	18
63	New simple proofs of the two-port stability criterium in terms of the single stability parameter $\hat{\Gamma}_{1/4/sub 1/}$ ( $\hat{\Gamma}_{1/4/sub 2/}$ ). IEEE Transactions on Microwave Theory and Techniques, 2001, 49, 1073-1076.	2.9	17
64	Self-consistent coupled carrier transport full-wave EM analysis of semiconductor traveling-wave devices. IEEE Transactions on Microwave Theory and Techniques, 2006, 54, 1611-1618.	2.9	17
65	A novel smart caliper foam pig for low-cost pipeline inspection " Part B: Field test and data processing. Journal of Petroleum Science and Engineering, 2015, 133, 771-775.	2.1	17
66	Multi-Gate FinFET Mixer Variability Assessment Through Physics-Based Simulation. IEEE Electron Device Letters, 2017, 38, 1004-1007.	2.2	17
67	High-resolution self-consistent thermal modelling of multi-gate power GaAs MESFETs. , 0, , .		15
68	3.5 GHz WiMAX GaN doherty power amplifier with second harmonic tuning. Microwave and Optical Technology Letters, 2012, 54, 2601-2605.	0.9	15
69	Large-Signal Stability of Symmetric Multibranch Power Amplifiers Exploiting Floquet Analysis. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 1580-1587.	2.9	15
70	Deriving $k\hat{A}\cdot p$ parameters from full-Brillouin-zone descriptions: A finite-element envelope function model for quantum-confined wurtzite nanostructures. Journal of Applied Physics, 2014, 116, 033709.	1.1	15
71	Efficient Sensitivity and Variability Analysis of Nonlinear Microwave Stages Through Concurrent TCAD and EM Modeling. IEEE Journal on Multiscale and Multiphysics Computational Techniques, 2019, 4, 356-363.	1.4	15
72	Neural networks and volterra series for time-domain power amplifier behavioral models. International Journal of RF and Microwave Computer-Aided Engineering, 2007, 17, 160-168.	0.8	14

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73	Simulation and design of OFET RFIDs through an analog/digital physics-based library. Organic Electronics, 2011, 12, 1328-1335.	1.4	14
74	Physics-based SS and SSLS variability assessment of microwave devices through efficient sensitivity analysis. , 2012, , .		14
75	Demonstration of inkjet-printed silver nanoparticle microstrip lines on alumina for RF power modules. Organic Electronics, 2014, 15, 91-98.	1.4	14
76	Accurate large-signal GaAs MESFET and HEMT modeling for power MMIC amplifier design. The International Executive, 1995, 5, 195-209.	0.2	13
77	A closed-form CAD-oriented model for the high-frequency conductor attenuation of symmetrical coupled coplanar waveguides. IEEE Transactions on Microwave Theory and Techniques, 1997, 45, 1065-1070.	2.9	13
78	Power PiN diode model for PSPICE simulations. , 0, , .		13
79	Reducing inter-pixel crosstalk in HgCdTe detectors. Optical and Quantum Electronics, 2020, 52, 1.	1.5	13
80	Physics-based RF noise modeling of submicron MOSFETs. , 0, , .		12
81	Physics-based modeling of submicron GaN permeable base transistors. IEEE Electron Device Letters, 2002, 23, 303-305.	2.2	12
82	When self-consistency makes a difference. IEEE Microwave Magazine, 2008, 9, 81-89.	0.7	12
83	Trap-assisted tunneling in InGaN/GaN LEDs: Experiments and physics-based simulation. , 2014, , .		12
84	Experimental investigation of bias current and load modulation effects in phase distortion of GaN HEMTs. Electronics Letters, 2014, 50, 773-775.	0.5	12
85	Model for carrier capture time through phonon emission in InGaN/GaN quantum wells. Physica Status Solidi (B): Basic Research, 2015, 252, 971-976.	0.7	12
86	New analytical approach for computing DC unipolar corona losses. IEE Proceedings A: Physical Science Measurement and Instrumentation Management and Education Reviews, 1984, 131, 318.	0.1	11
87	Sensitivity-based optimization and statistical analysis of microwave semiconductor devices through multidimensional physical simulation (invited article). The International Executive, 1997, 7, 129-143.	0.2	11
88	Failure analysis of travelling wave MSM distributed photodetectors. , 0, , .		11
89	Simulation of Carrier Transport in Wide Band Gap Semiconductors. International Journal of High Speed Electronics and Systems, 2001, 11, 525-584.	0.3	11
90	Guest Editorial Special Issue on GaN Electronic Devices. IEEE Transactions on Electron Devices, 2013, 60, 2975-2981.	1.6	11

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91	Modeling Photocurrent Spectra of Single-Color and Dual-Band HgCdTe Photodetectors: Is 3D Simulation Unavoidable?. Journal of Electronic Materials, 2014, 43, 3070-3076.	1.0	11
92	Physics-based modeling of FinFET RF variability. , 2016, , .		11
93	Electroluminescence Analysis and Simulation of the Effects of Injection and Temperature on Carrier Distribution in InGaN-Based Light-Emitting Diodes with Color-Coded Quantum Wells. Japanese Journal of Applied Physics, 2013, 52, 08JG09.	0.8	10
94	A K-band GaAs MMIC Doherty power amplifier for point-to-point microwave backhaul applications. , 2014, , .		10
95	13-bit GaAs serial-to-parallel converter with compact layout for core-chip applications. Microelectronics Journal, 2014, 45, 864-869.	1.1	10
96	Analysis of Carrier Transport in Tunnel-Junction Vertical-Cavity Surface-Emitting Lasers by a Coupled Nonequilibrium Greenâ€™s Functionâ€™Drift-Diffusion Approach. Physical Review Applied, 2020, 14, .	1.5	10
97	A new, efficient approach to the large-scale thermal modeling of III-V devices and integrated circuits. , 0, , .		9
98	Compact Conversion and Cyclostationary Noise Modeling of pnâ€™Junction Diodes in Low-Injectionâ€™Part I: Model Derivation. IEEE Transactions on Electron Devices, 2004, 51, 467-476.	1.6	9
99	Compact Conversion and Cyclostationary Noise Modeling of pnâ€™Junction Diodes in Low-Injectionâ€™Part II: Discussion. IEEE Transactions on Electron Devices, 2004, 51, 477-485.	1.6	9
100	Accurate large-signal equivalent circuit of surface channel diamond FETs based on the Chalmers model. Diamond and Related Materials, 2012, 26, 15-19.	1.8	9
101	X-band wideband 5W GaN MMIC power amplifier with large-signal gain equalization. , 2012, , .		9
102	Consistent static and small-signal physics-based modeling of dye-sensitized solar cells under different illumination conditions. Physical Chemistry Chemical Physics, 2013, 15, 14634.	1.3	9
103	Investigating the properties of interfacial layers in planar Schottky contacts on hydrogen-terminated diamond through direct current/small-signal characterization and radial line small-signal modelling. Applied Physics Letters, 2015, 106, .	1.5	9
104	Electrical Effects of a Single Extended Defect in MOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 3069-3075.	1.6	9
105	Heterostructure modeling considerations for Ge-on-Si waveguide photodetectors. Optical and Quantum Electronics, 2018, 50, 1.	1.5	9
106	FDTD simulation of compositionally graded HgCdTe photodetectors. Infrared Physics and Technology, 2019, 97, 203-209.	1.3	9
107	Plasmonic-organic hybrid electro/optic Mach-Zehnder modulators: from waveguide to multiphysics modal-FDTD modeling. Optics Express, 2020, 28, 29253.	1.7	9
108	Constraints and performance trade-offs in Auger-suppressed HgCdTe focal plane arrays. Applied Optics, 2020, 59, E1.	0.9	9



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109	Inverse scattering for optical couplers. Exact solution of Marchenko equations. Journal of Mathematical Physics, 1984, 25, 1900-1904.	0.5	8
110	Thermal analysis of power GaAs MESFETs. , 1987, , .		8
111	An efficient, CAD-oriented model for the characteristic parameters of multiconductor buses in high-speed digital GaAs ICs. Analog Integrated Circuits and Signal Processing, 1994, 5, 67-75.	0.9	8
112	Assessment of Thermal Instabilities and Oscillations in Multifinger Heterojunction Bipolar Transistors Through a Harmonic-Balance-Based CAD-Oriented Dynamic Stability Analysis Technique. IEEE Transactions on Microwave Theory and Techniques, 2009, 57, 3461-3468.	2.9	8
113	Fast Exact Inversion of the Generalized Zakharov-Shabat Problem for Rational Scattering Data: Application to the Synthesis of Optical Couplers. SIAM Journal on Applied Mathematics, 1988, 48, 689-702.	0.8	7
114	High-field diffusivity and noise spectra in GaAs MESFETs. Journal Physics D: Applied Physics, 1994, 27, 365-375.	1.3	7
115	Analysis of failure mechanisms in velocity-matched distributed photodetectors. IEE Proceedings: Optoelectronics, 1999, 146, 25-30.	0.8	7
116	Exact, conformal-mapping models for the high-frequency losses of coplanar waveguides with thick electrodes of rectangular or trapezoidal cross section. , 0, , .		7
117	Simplex Algorithm for Band Structure Calculation of Noncubic Symmetry Semiconductors: Application to III-nitride Binaries and Alloys. VLSI Design, 2001, 13, 63-68.	0.5	7
118	Compact modelling of cyclostationary noise in semiconductor devices: a critical discussion. , 0, , .		7
119	Finite Difference Based Power Diodes Simulation Within SPICE: Modeling Approach and Validation. , 0, , .		7
120	Large-signal device simulation in time- and frequency-domain: a comparison. COMPEL - the International Journal for Computation and Mathematics in Electrical and Electronic Engineering, 2008, 27, 1319-1325.	0.5	7
121	Compact GaAs HEMT D flip-flop for the integration of a SAR MMIC core-chip digital control logic. , 2010, , .		7
122	Development of single-stage and doherty GaN-based hybrid RF power amplifiers for quasi-constant envelope and high peak to average power ratio wireless standards. Microwave and Optical Technology Letters, 2012, 54, 206-210.	0.9	7
123	An overview on recent developments in RF and microwave power H-terminated diamond MESFET technology. , 2014, , .		7
124	Computer interpretation of carotid waves using a knowledge based system. Signal Processing, 1982, 4, 409-423.	2.1	6
125	Large-scale, computer-aided thermal design of power GaAs integrated devices and circuits. , 0, , .		6
126	Simulation of Carrier Transport in Wide Band Gap Semiconductors. Selected Topics in Electornics and Systems, 2001, , 163-222.	0.2	6



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127	Design, Fabrication and Characterization of $1.5 \mu\text{m} \times 2 \mu\text{m}$ , 800 V 4H-SiC n-Type Schottky Barrier Diodes. Materials Science Forum, 2005, 483-485, 941-944.	0.3	6
128	GaN Device Technology: Manufacturing, Characterization, Modelling and Verification. , 2008, , .		6
129	A Generalized Drift-Diffusion Model for Rectifying Schottky Contact Simulation. IEEE Transactions on Electron Devices, 2010, 57, 1539-1547.	1.6	6
130	Numerical study of thin-film quantum-dot solar cells combining selective doping and light-trapping approaches. , 2016, , .		6
131	Challenges towards the simulation of GaN-based LEDs beyond the semiclassical framework. Proceedings of SPIE, 2016, , .	0.8	6
132	Non-Monochromatic 3D Optical Simulation of HgCdTe Focal Plane Arrays. Journal of Electronic Materials, 2018, 47, 5742-5751.	1.0	6
133	Looking for Quality in TCAD-Based Papers. IEEE Transactions on Electron Devices, 2019, 66, 3252-3253.	1.6	6
134	Generalized Symmetrical 3 dB Power Dividers With Complex Termination Impedances. IEEE Access, 2020, 8, 38239-38247.	2.6	6
135	A new approach to the physics-based noise analysis of semiconductor devices operating in large signal, (quasi) periodic regime. , 0, , .		5
136	Design and characterization of a 10-Gb/s dual-drive Z-cut Ti:LiNbO <sub>3</sub> electrooptical modulator. Journal of Lightwave Technology, 2006, 24, 2355-2361.	2.7	5
137	Novel TCAD-Oriented Definition of the off-State Breakdown Voltage in Schottky-Gate FETs: A 4H-SiC MESFET Case Study. IEEE Transactions on Electron Devices, 2008, 55, 3347-3353.	1.6	5
138	SPICE Library for Low-Cost RFID Applications Based on Pentacene Organic FET. , 2010, , .		5
139	GaN Monolithic Power Amplifiers for Microwave Backhaul Applications. Electronics (Switzerland), 2016, 5, 25.	1.8	5
140	Challenges in multiphysics modeling of dual-band HgCdTe infrared detectors. Applied Optics, 2020, 59, 5656.	0.9	5
141	Evaluating the impedance field through several transport models: A comparison. Journal of Applied Physics, 1999, 85, 2192-2196.	1.1	4
142	GREEN'S FUNCTIONS APPROACH TO MOS PHYSICS-BASED COMPACT NOISE MODELLING. Fluctuation and Noise Letters, 2001, 01, R51-R63.	1.0	4
143	Multisectional modeling of high-speed electrooptic modulators integrated in a microwave circuit CAD environment. Journal of Lightwave Technology, 2003, 21, 2989-2996.	2.7	4
144	Immittance and $S$ -Parameter-Based Criteria for the Unconditional Stability of Linear Two-Ports: Relations and Invariance Properties. IEEE Transactions on Microwave Theory and Techniques, 2009, 57, 519-523.	2.9	4

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145	FPGA Implementation of Adaptive Baseband Predistortion for FET-Based Wireless Power Amplifiers. , 2009, , .		4
146	Floquet-Based Stability Analysis of Power Amplifiers Including Distributed Elements. IEEE Microwave and Wireless Components Letters, 2014, 24, 493-495.	2.0	4
147	A Novel TCAD Approach to Temperature Dependent DC FinFET Variability Analysis. , 2018, , .		4
148	Physical noise modelling of majority-carrier devices: an adjoint-network approach. , 0, , .		3
149	New, closed-form compact model for the cyclostationary noise and LS conversion behaviour of RF junction diodes. , 0, , .		3
150	Comments on "Noise source modeling for cyclostationary noise analysis in large-signal device operation". IEEE Transactions on Electron Devices, 2003, 50, 2183.	1.6	3
151	Evaluation of GaN HEMT Technology Development Through Nonlinear Characterization. , 0, , .		3
152	A 20 Watt Micro-strip X-Band AlGaIn/GaN HPA MMIC for Advanced Radar Applications. , 2008, , .		3
153	Assessment of surge current capabilities of SiC-based high-power diodes through physics-based mixed-mode electro-thermal simulations. , 2009, , .		3
154	A 22W 65% efficiency GaN Doherty Power Amplifier at 3.5 GHz for WiMAX applications. , 2011, , .		3
155	Bandwidth extension of GaN Doherty power amplifier: Effect on power, efficiency and linearity. , 2013, , .		3
156	A green's function approach to the analysis of non volatile memory device variability as a function of individual trap position. , 2013, , .		3
157	Assessment of silver nanoparticle inkjet-printed microstrip lines for RF and microwave applications. , 2013, , .		3
158	Application of Floquet theory to the large signal stability analysis of microwave amplifiers. , 2013, , .		3
159	Broadband 3D optical modeling of HgCdTe infrared focal plane arrays. , 2017, , .		3
160	Organic Electro-Optic Mach-Zehnder Modulators: From Physics-Based to System-Level Modeling. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100390.	0.8	3
161	A new general-purpose two-dimensional mesh generator for finite elements, generalized finite differences, and moment method applications. IEEE Transactions on Magnetics, 1988, 24, 307-310.	1.2	2
162	A new dynamic, self-consistent electro-thermal model of power HBTs and a novel interpretation of thermal collapse loci in multi-finger devices. , 0, , .		2

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163	Physics-based Mixer Noise Simulation. , 2006, , .		2
164	Fabrication, Characterization and Numerical Simulation of High Breakdown Voltage pHEMTs. , 2006, , .		2
165	Low-frequency noise conversion modeling in RF devices under forced nonlinear operation. International Journal of RF and Microwave Computer-Aided Engineering, 2006, 16, 4-12.	0.8	2
166	Theoretical investigation of GaN permeable base transistors for microwave power applications. Semiconductor Science and Technology, 2006, 21, 13-18.	1.0	2
167	Innovative techniques for device large-signal noise simulations. AIP Conference Proceedings, 2007, , .	0.3	2
168	From device characterization to system level analysis of dual band PA design in SiGe technology. International Journal of RF and Microwave Computer-Aided Engineering, 2008, 18, 552-563.	0.8	2
169	A novel, rigorous approach to the dynamic, large-signal stability analysis of semiconductor devices and circuits under electro-thermal interaction. , 2008, , .		2
170	Concurrent dual-band SiGe HBT power amplifier for Wireless applications. International Journal of Microwave and Wireless Technologies, 2009, 1, 117-126.	1.5	2
171	A device-level analog and digital subsystem SPICE library for the design of low-cost pentacene OFET RFIDs. , 2010, , .		2
172	7 GHz GaN MMIC power amplifier for Microwave Radio links with 45% drain efficiency in a wide power range. , 2010, , .		2
173	Advanced GaN-based high frequency power amplifiers. , 2013, , .		2
174	System level characterization and digital predistortion of GaN MMIC Doherty power amplifiers for microwave point-to-point radios. , 2014, , .		2
175	Modeling the Conductor Losses of Thick Multiconductor Coplanar Waveguides and Striplines: A Conformal Mapping Approach. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 1217-1227.	2.9	2
176	Large-signal variability of microwave power amplifiers through efficient device sensitivity-based physical modeling. International Journal of RF and Microwave Computer-Aided Engineering, 2017, 27, e21099.	0.8	2
177	Variability of FinFET AC parameters: A physics-based insight. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2018, 31, e2285.	1.2	2
178	Physically-based statistical analysis of nonlinear circuits through X-parameters. , 2019, , .		2
179	Simulation of electro optic modulators based on plasmonic directional couplers. , 2020, , .		2
180	Quantum Efficiency and Crosstalk in Subwavelength HgCdTe Dual Band Infrared Detectors. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-9.	1.9	2

#	ARTICLE	IF	CITATIONS
181	NOISE MODELING FOR PDE BASED DEVICE SIMULATIONS. , 2001, , .		2
182	FUNDAMENTAL AND EQUIVALENT CYCLOSTATIONARY MICROSCOPIC NOISE SOURCES FOR LS DEVICE SIMULATION. , 2001, , .		2
183	An Efficient, CAD-Oriented Model for the Characteristic Parameters of Multiconductor Buses in High-Speed Digital GaAs ICs. , 1994, , 67-75.		2
184	Large-signal E/O modelling of traveling-wave electroabsorption modulators in an RF circuit CAD environment. , 0, , .		1
185	An extended majority-carrier approach for the DC and small-signal simulation of ion-implanted mesfets on compensated and p-type substrates. European Transactions on Telecommunications, 1990, 1, 411-419.	1.2	1
186	Device simulation. , 1991, , 89-144.		1
187	Fast steady-state algorithms for the analysis of nonlinear dispersive, distributed planar electromagnetic structures, excited by periodic waveforms. IEEE Transactions on Magnetics, 1994, 30, 3172-3175.	1.2	1
188	A new, compact model for high-speed electro-optic modulators fully integrated within a microwave CAD environment. , 0, , .		1
189	Fast higher-order full-wave FEM analysis of traveling-wave optoelectronic devices. , 2001, , .		1
190	<title>Simultaneous suppression of laser relative intensity noise: second- and third-order distortions using a balanced electro-absorption modulator</title>. , 2001, , .		1
191	Self-consistent time-domain large signal model of traveling-wave electroabsorption modulators. , 0, , .		1
192	A new analytical model for high frequency MOSFET noise. , 0, , .		1
193	FEM-based reduced-order model for steady-state skin-effect analysis in lossy lines. , 0, , .		1
194	Key issues in trap-assisted low-frequency device noise simulation in nonlinear large-signal conditions. AIP Conference Proceedings, 2005, , .	0.3	1
195	Simulation of switched-mode power supplies (SMPS) through an accurate non-quasi-static SPICE power diode model. , 2005, , .		1
196	An efficient numerical technique for the implementation of SSSL and cyclostationary noise analysis in physics-based device simulators. Journal of Computational Electronics, 2006, 5, 85-89.	1.3	1
197	Application of physical models to circuit simulations. , 2007, , .		1
198	HB-based CAD-oriented dynamic stability analysis of circuits and devices: Application to the assessment of thermal instabilities in multifinger HBTs. , 2009, , .		1

#	ARTICLE	IF	CITATIONS
199	RF power performance of submicron MESFET on hydrogen terminated polycrystalline diamond. , 2009, , .		1
200	A device-level analog and digital subsystem SPICE library for the design of low-cost pentacene OFET RFIDs. , 2010, , .		1
201	Modeling and simulation of noise in transistors under large-signal condition. , 2011, , .		1
202	GaN MMIC Doherty power amplifier solutions for backhaul microwave links. , 2013, , .		1
203	A surface-potential-based MOSFET compact model accounting for random doping fluctuations. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2014, 27, 748-760.	1.2	1
204	A 2-watt, 0.15-W GaAs pHEMT stacked amplifier at 22 GHz. , 2014, , .		1
205	Single-crystal diamond microwave devices for space applications. , 2014, , .		1
206	Improved phase linearity in source field plate AlGaIn/GaN HEMTs. , 2014, , .		1
207	Evaluating GaN Doherty architectures for 4G Picocells, WiMax and microwave backhaul links. , 2014, , .		1
208	Improved phase linearity in Source Field Plate AlGaIn/GaN HEMTs. , 2014, , .		1
209	TCAD analysis of FinFET temperature-dependent variability for analog applications. , 2019, , .		1
210	Plasmon-Enhanced Light Absorption in Mid-Wavelength Infrared HgCdTe Detectors. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-10.	1.9	1
211	Comments on "Capacitance Between Perpendicular Conducting Planes Separated by a Gap". IEEE Transactions on Electromagnetic Compatibility, 1987, EMC-29, 252-255.	1.4	0
212	Comments on numerical large-signal simulation of the diffusion noise in GaAs Gunn devices" [with reply]. IEEE Transactions on Electron Devices, 1993, 40, 1902-1903.	1.6	0
213	An extended fukui-like formula for the minimum-noise figure of microwave fets. Microwave and Optical Technology Letters, 1994, 7, 555-559.	0.9	0
214	Advanced Cad Models. , 1996, , 203-250.		0
215	Balanced electroabsorption modulated RF photonic link. , 0, , .		0
216	Computer-aided design and optimization of high-speed electro-optic modulators: integrating the RF and EO models within a unified environment. , 0, , .		0

#	ARTICLE	IF	CITATIONS
217	Small- and large-signal trap-assisted GR noise modeling in semiconductor devices. , 2004, 5470, 37.		0
218	Simulation of cyclostationary noise in semiconductor devices. , 2004, , .		0
219	Two-dimensional physics-based low-frequency noise modeling of bipolar semiconductor devices in small- and large-signal operation. AIP Conference Proceedings, 2005, , .	0.3	0
220	Accurate simulation of travelling-wave electroabsorption modulators through a novel coupled electromagnetic and carrier-transport model. , 2005, , .		0
221	GaN HEMT Technology Development Assessment through Nonlinear Characterization. , 2006, , .		0
222	Quantum, Power, and Compound Semiconductor Devices -- Devices and Passives for Si RF Power. , 2006, , .		0
223	Kinetic and Partial-Differential Equation Modeling of Noise in Schottky Barrier Diodes: a Comparison. AIP Conference Proceedings, 2007, , .	0.3	0
224	Hydrodynamic transport parameters of wurtzite ZnO from analytic- and full-band Monte Carlo Simulation. , 2007, , .		0
225	Quantum, Power, &#x0026; Compound Semiconductors - Ultra High Speed SiGe and InP-based HBTs. , 2007, , .		0
226	A 2.469&#x223C;2.69GHz AlGaIn/GaN HEMT power amplifier for IEEE 802.16e WiMAX applications. , 2008, , .		0
227	Behavioral modeling of GaN&#x2013;based power amplifiers: Impact of electrothermal feedback on the model accuracy and identification. Microwave and Optical Technology Letters, 2009, 51, 2789-2792.	0.9	0
228	A spurious-solution-free envelope function model for quantum-confined wurtzite nanostructures. , 2014, , .		0
229	Microscopic models of non-radiative and high-current effects in LEDs: state of the art and future developments. Proceedings of SPIE, 2014, , .	0.8	0
230	Cyclostationary noise modeling of radio frequency devices. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2015, 28, 659-674.	1.2	0
231	Kudos To Our Reviewers. IEEE Transactions on Electron Devices, 2015, 62, 3905-3905.	1.6	0
232	Kudos to Our Reviewers. IEEE Transactions on Electron Devices, 2016, 63, 4557-4557.	1.6	0
233	Electrically Controlled Photocatalytic Reduction of Graphene Oxide Sheets by ZnO Nanostructures, Suitable for Tunable Optoelectronic Applications. IEEE Transactions on Electron Devices, 2016, , 1-7.	1.6	0
234	Microwave Linear Amplifiers. , 0, , 261-351.		0

#	ARTICLE	IF	CITATIONS
235	Power Amplifiers. , 0, , 411-488.		0
236	Kudos to Our Reviewers. IEEE Transactions on Electron Devices, 2017, 64, 4776-4776.	1.6	0
237	Changes in the Editorial Board. IEEE Transactions on Electron Devices, 2017, 64, 4372-4373.	1.6	0
238	Corrections to "Analytic Determination of the Capacitance Matrix of Planar or Cylindrical Multiconductor Lines on Multilayered Substrates" [Feb 95 363-373]. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 2284-2284.	2.9	0
239	Modeling Techniques for Electronic Noise and Process Variability in Nanoscale Devices. , 2018, , .		0
240	Kudos to Our Reviewers. IEEE Transactions on Electron Devices, 2018, 65, 5227-5227.	1.6	0
241	Enhanced semiclassical simulation of InGaN/GaN multi-quantum-well solar cells. , 2019, , .		0
242	Kudos to Our Reviewers. IEEE Transactions on Electron Devices, 2019, 66, 5024-5024.	1.6	0
243	Reducing inter-pixel crosstalk in HgCdTe detectors. , 2019, , .		0
244	Challenges in multiphysics modeling of dual-band HgCdTe infrared detectors. , 2020, , .		0
245	Towards an efficient simulation framework for plasmonic organic hybrid E/O modulators. , 2020, , .		0
246	Fabrication of Microsensor for Detection of Low-Concentration Formaldehyde Gas in Formalin-Treated Fish. IEEE Transactions on Electron Devices, 2020, 67, 5257-5261.	1.6	0
247	Editorial Special Section on Papers From the 2020 VLSI Symposium. IEEE Transactions on Electron Devices, 2020, 67, 5305-5305.	1.6	0
248	Changes in the Editorial Board. IEEE Transactions on Electron Devices, 2020, 67, 773-776.	1.6	0
249	Changes in the Editorial Board. IEEE Transactions on Electron Devices, 2021, 68, 1398-1399.	1.6	0
250	Plasmonic nanorods for enhanced absorption in mid-wavelength infrared detectors. , 2021, , .		0
251	Accurate and efficient numerical quasi-TEM modeling of coplanar waveguides for high-speed electro-optic modulators. , 2021, , .		0
252	Kudos to Our Reviewers. IEEE Transactions on Electron Devices, 2020, 67, 5262-5262.	1.6	0



#	ARTICLE	IF	CITATIONS
253	Efficient TCAD Large-Signal temperature-dependent variability analysis of a FinFET power amplifier. , 2021, , .		0
254	Editorial Special Section on ESSDERC. IEEE Transactions on Electron Devices, 2020, 67, 4558-4558.	1.6	0
255	Analysis and Design of Plasmonic-Organic Hybrid Electro-Optic Modulators Based on Directional Couplers. IEEE Photonics Journal, 2022, 14, 1-11.	1.0	0
256	Kudos to Our Reviewers. IEEE Transactions on Electron Devices, 2021, 68, 5933-5933.	1.6	0